

BEST AVAILABLE COPY

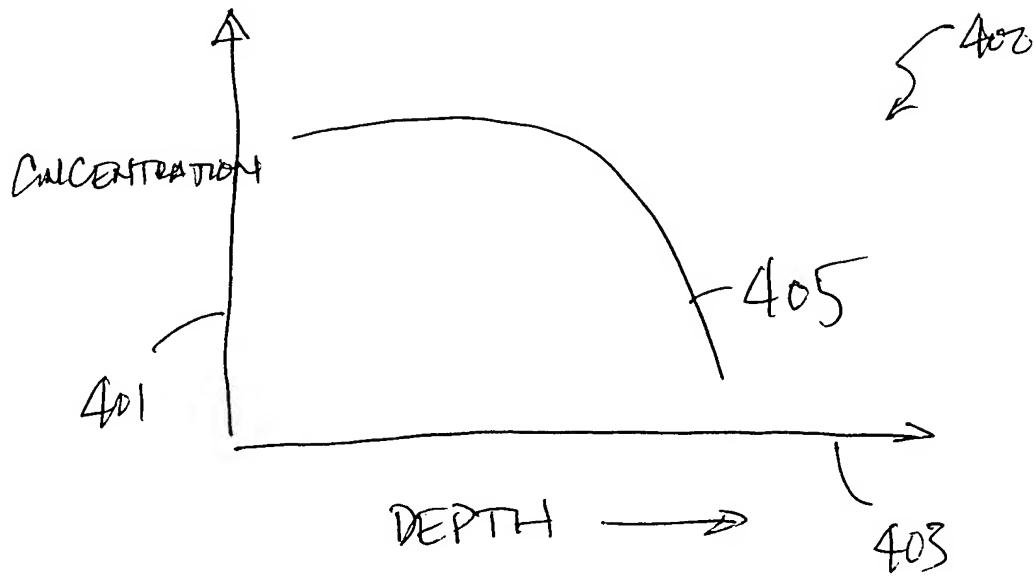


FIG. 4

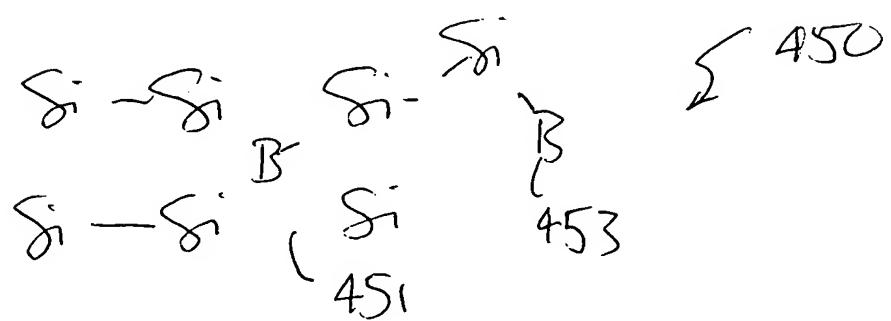


FIG. 4A

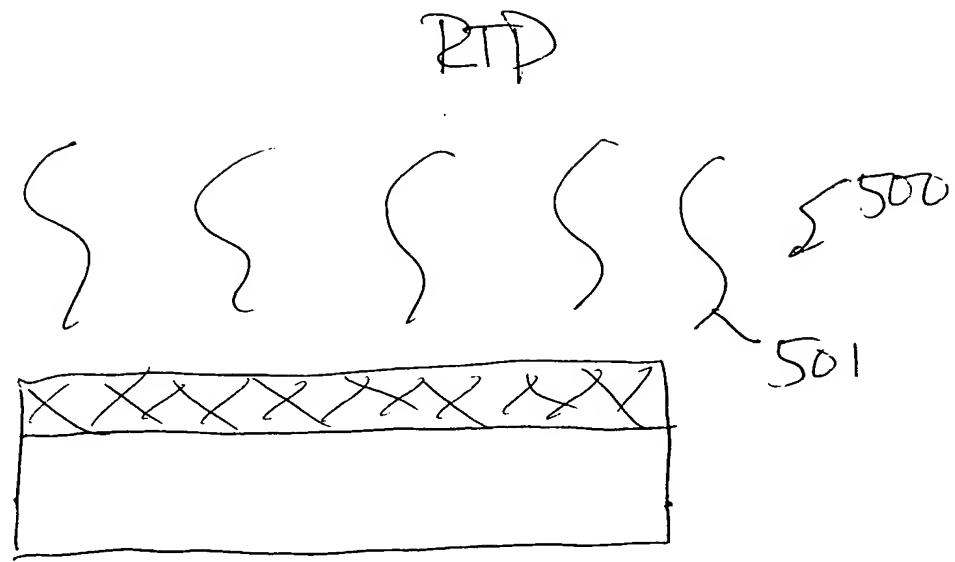


FIG. 5

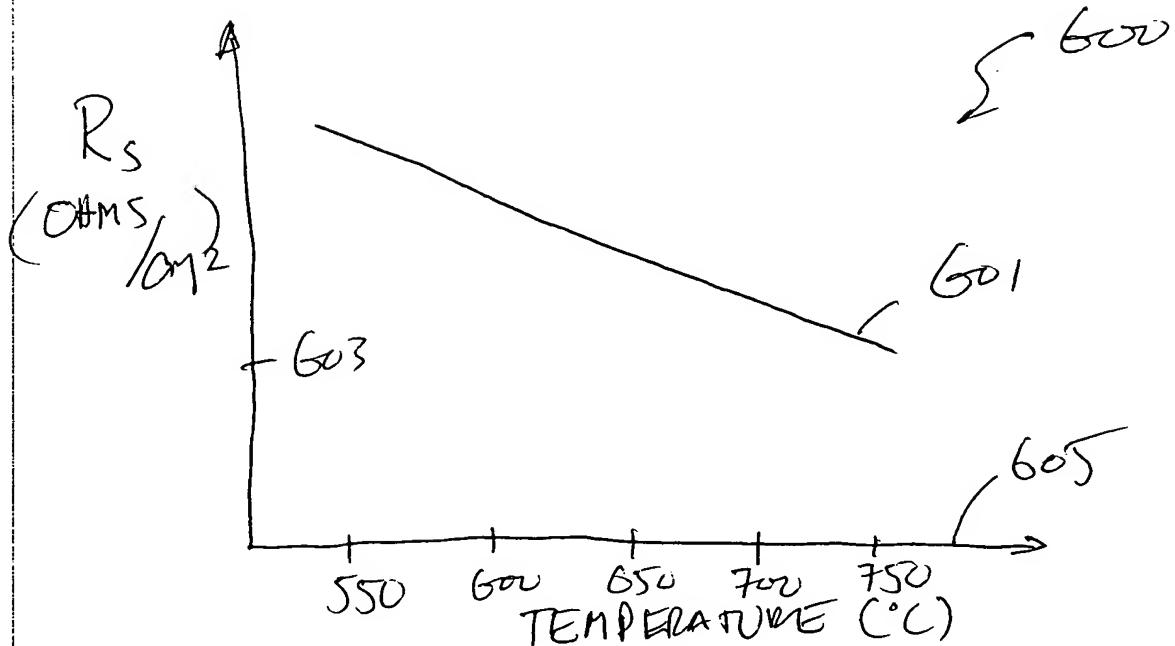


FIG. 6

Low temperature monitor

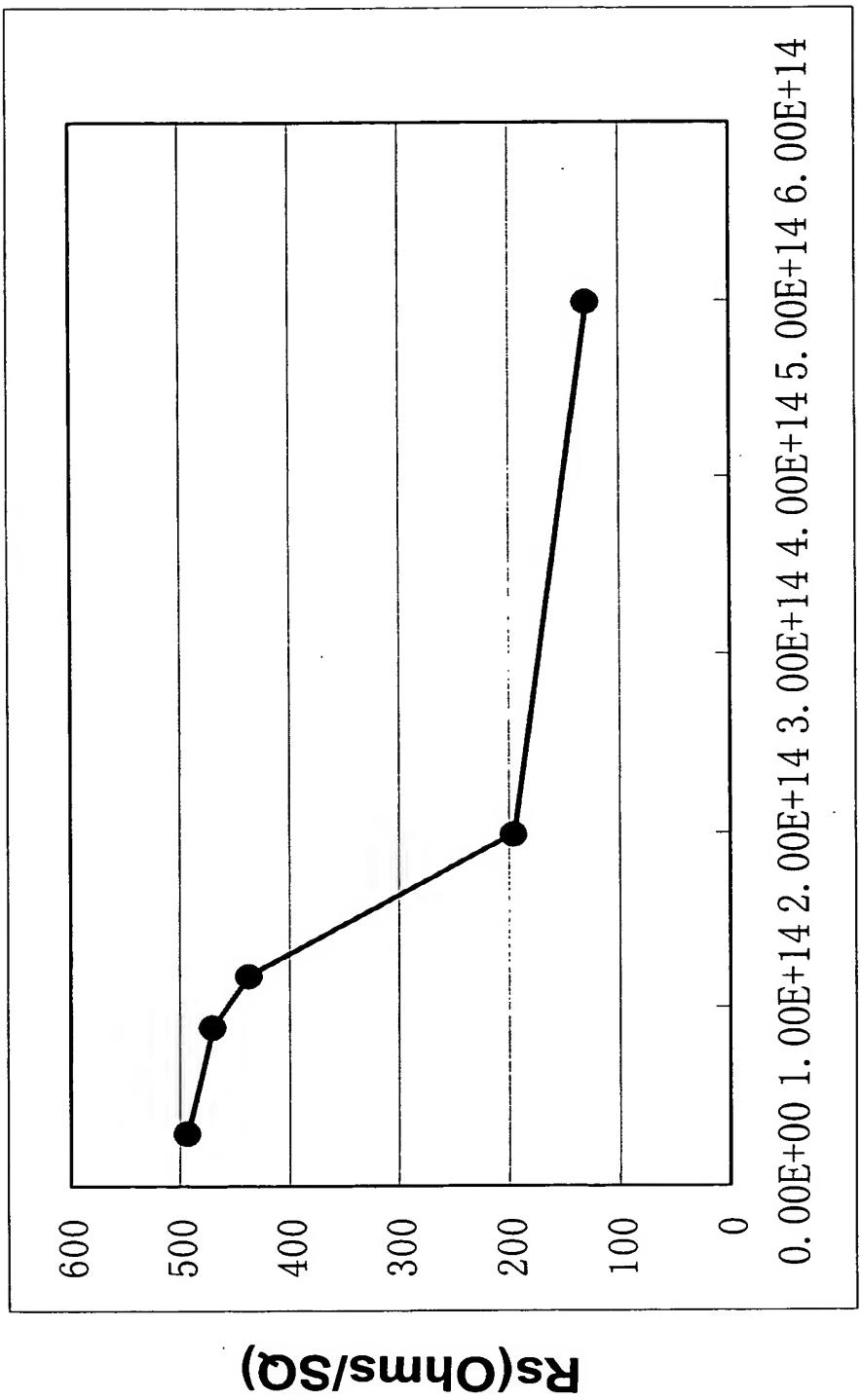


Figure 7: Changes of R_s as a function of implant dosage of silicon,
Boron dosage unchanged($3.5E15$).
F/G. 7

Low temperature monitor

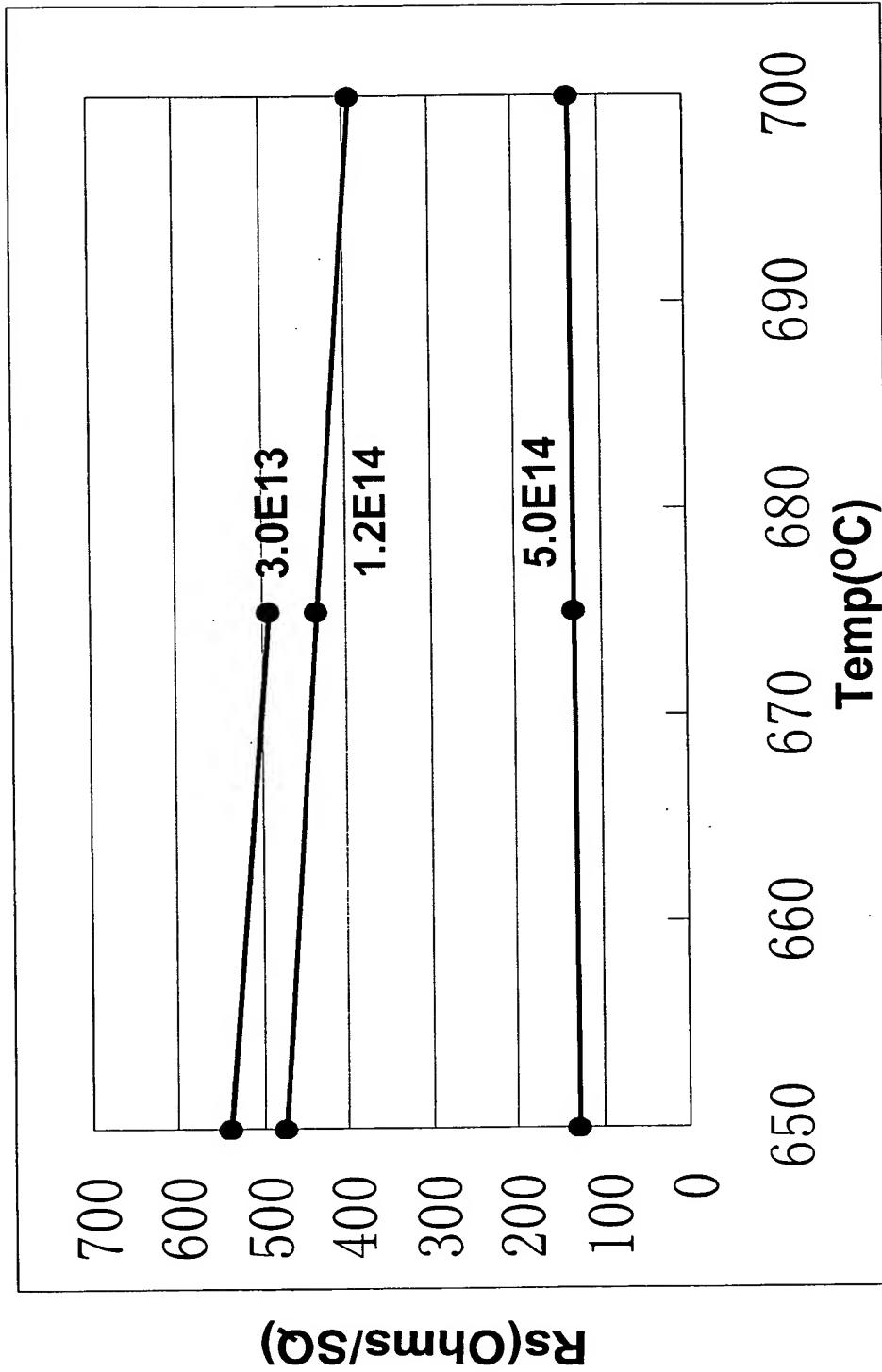


Figure 8: The dependence of Rs on annealing temperature. The implant dose of silicon varied from $3.0E13$ to $5.0E14$, Boron dosage unchanged($3.5E15$).